Power and Hybrid SILICON SWITCHING NPN TRANSISTOR



2N2222ACSM

- High Speed Saturated Switching
- Hermetic Ceramic Surface Mount Package
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

V _{CBO}	Collector – Base Voltage		75V
V_{CEO}	Collector – Emitter Voltage		40V
V_{EBO}	Emitter – Base Voltage		6V
IC	Continuous Collector Current		0.8A
P_{D}	Total Power Dissipation at	$T_A = 25$ °C	500mW
		Derate Above 25°C	2.86mW/°C
T _J	Junction Temperature Range		-65 to +200°C
T _{stg}	Storage Temperature Range		-65 to +200°C

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction To Ambient	350	°C/W

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise stated)

Symbols	Parameters	Test Conditions		Min.	Тур.	Max.	Units	
V _{(BR)CEO} ⁽¹⁾	Collector-Emitter Breakdown Voltage	I _C = 10mA	40			V		
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10μA	75					
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10μA		6				
I _{CEX}	Collector-Emitter Cut-Off Current	V _{EB} = 3V	V _{CE} = 60V			10	nA	
lono	Collector-Base Cut-Off Current	I _E = 0	$V_{CB} = 60V$	= 60V		10		
I _{СВО}			T _A = 150°C			10	μΑ	
I _{EBO}	Emitter Cut-Off Current	I _C = 0	V _{EB} = 3V			10	nA	
), (1)	Collector-Emitter Saturation Voltage	I _C = 150mA I _B = 15mA				0.3		
V _{CE(Sat)} ⁽¹⁾		I _C = 500mA	I _B = 50mA			1.0	.,	
V _{BE(Sat)} ⁽¹⁾	Base-Emitter Saturation Voltage	I _C = 150mA I _B = 15mA		0.6		1.2	V	
		I _C = 500mA	I _B = 50mA			2.0	1	
	DC Current Gain	I _C = 0.1mA	V _{CE} = 10V	35				
		I _C = 1.0mA		50				
h _{FE} ⁽¹⁾		I _C = 10mA	V _{CE} = 10V	75				
			T _A = -55°C	35			T -	
		I _C = 150mA		100		300	1	
				50			1	
		I _C = 500mA	V _{CE} = 10V	40			1	

DYNAMIC CHARACTERISTICS

C _{obo}	Output Capacitance	V _{CB} = 10V	I _E = 0	f = 1.0MHz		8	nΓ
c _{ibo}	Input Capacitance	V _{EB} = 0.5V	I _C = 0	f = 1.0MHz		30	pF
f _t	Transition Frequency	I _C = 20mA	V _{CE} = 20V	f = 100MHz	300		MHz
he	Small Signal Current Gain	I _C = 1.0mA	V _{CE} = 10V	f = 1.0kHz	50	300	-
h _{fe}		I _C = 10mA	V _{CE} = 10V	f = 1.0kHz	75	375	
^t d	Delay Time	V _{CC} = 30V	V _{BE} = 0.5V			10	
t _r	Rise Time	I _C = 150mA	I _{B1} = 15mA			25	200
t _s	Storage Time	V _{CC} = 30V	VBE = 0.5V			225	ns
t _f	Fall Time	I _C = 150mA	$I_{B1} = I_{B2} = 15r$	mA		60	

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Note

(1) Pulse Width $\leq 380 \mu s$, $\delta \leq 2\%$

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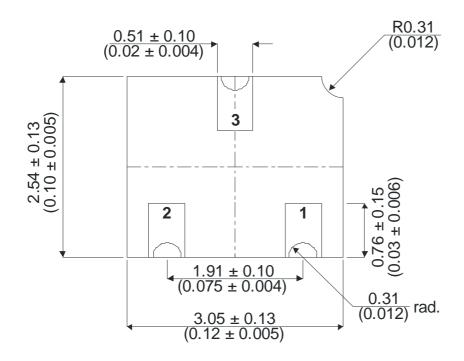
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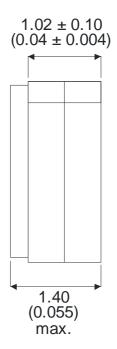
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MECHANICAL DATA

Dimensions in mm (inches)





LCC1

Underside View

Pad 1 - Base

Pad 2 - Emitter

Pad 3 - Collector

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